

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

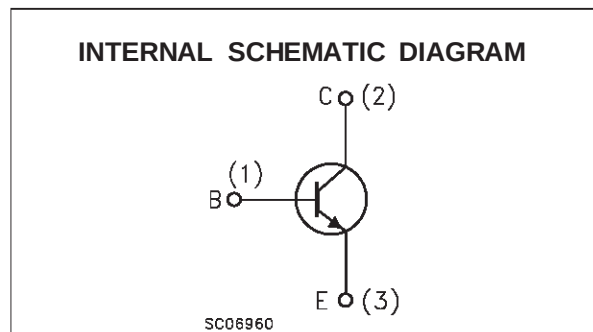
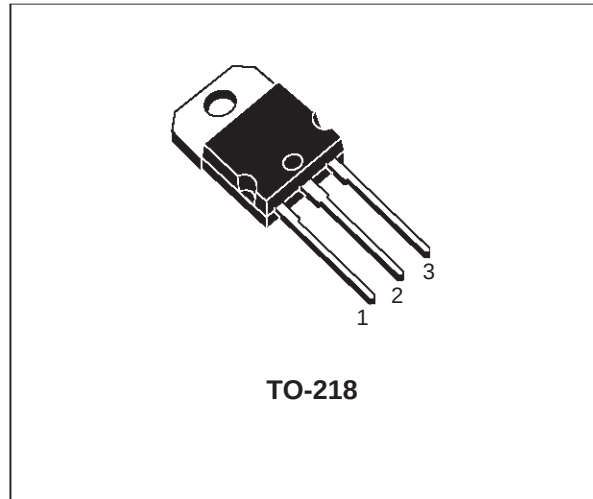
APPLICATIONS

- ELECTRONIC TRANSFORMER FOR HALOGEN LAMPS
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BUL810 is manufactured using high voltage Multiepitaxial Mesa technology for cost-effective high performance. It uses a Hollow Emitter structure to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	1000	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	450	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	9	V
I_C	Collector Current	15	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	22	A
I_B	Base Current	5	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	10	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	125	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

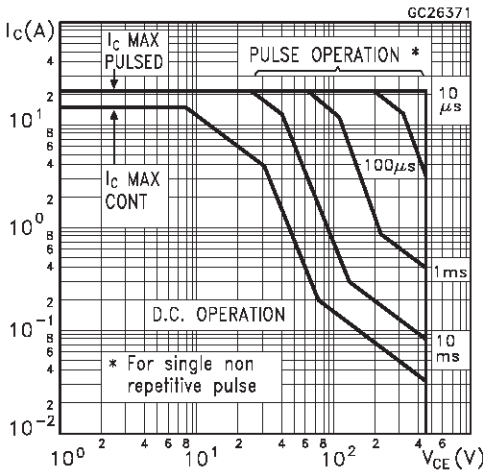
R _{thj-case}	Thermal Resistance Junction-Case	Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-Ambient	Max	30	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

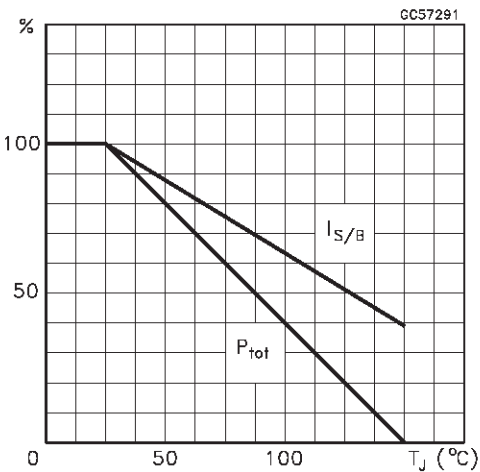
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1000 V V _{CE} = 1000 V T _j = 125 °C			100 500	μA μA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 450 V			250	μA
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 100 mA L = 25 mH	450			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 10 mA	9			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 5 A I _B = 1 A I _C = 8 A I _B = 1.6 A I _C = 12 A I _B = 2.4 A			1 1.5 5	V V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 5 A I _B = 1 A I _C = 8 A I _B = 1.6 A			1.3 1.6	V V
h _{FE*}	DC Current Gain	I _C = 5 A V _{CE} = 5 V I _C = 10 mA V _{CE} = 5 V	10 10		40	
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	I _C = 8 A I _{B1} = 1.6 A V _{BE(off)} = -5 V R _{BB} = 0.4 Ω V _{CL} = 350 V L = 200 μH		1.5 55	2.3 110	μs ns
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	I _C = 8 A I _{B1} = 1.6 A V _{BE(off)} = -5 V R _{BB} = 0.4 Ω V _{CL} = 350 V L = 200 μH T _j = 100 °C		1.9 80		μs ns

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

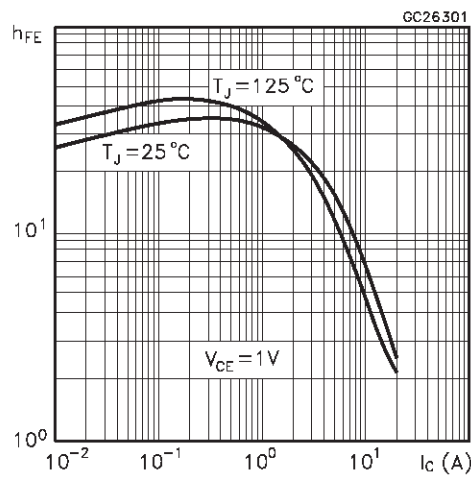
Safe Operating Areas



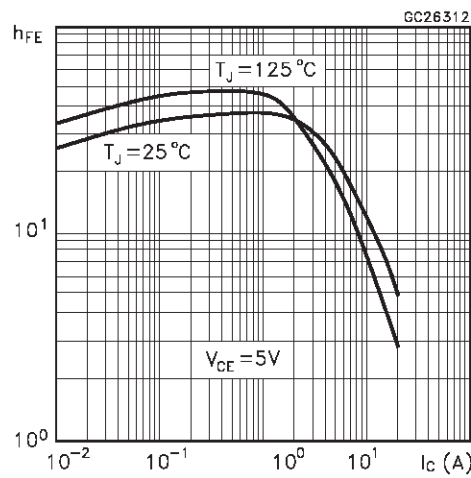
Derating Curve



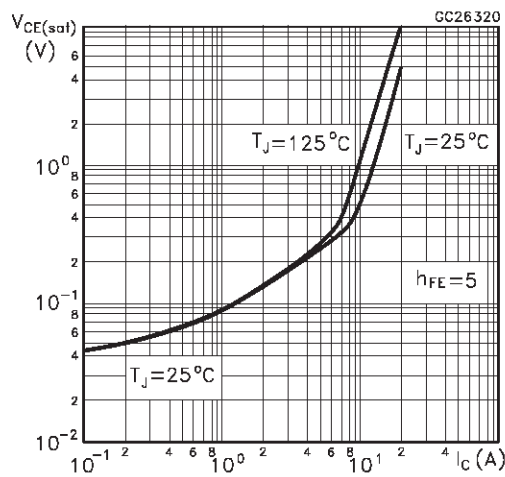
DC Current Gain



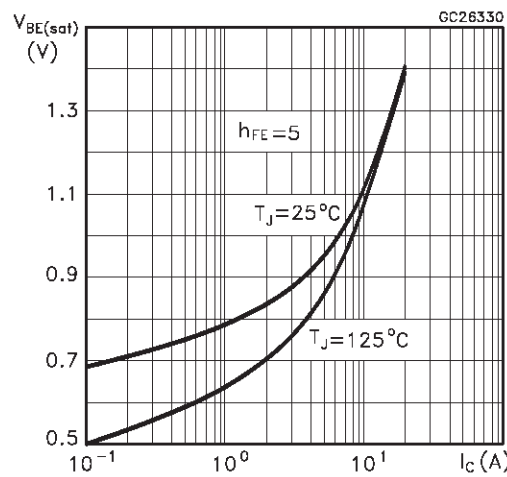
DC Current Gain



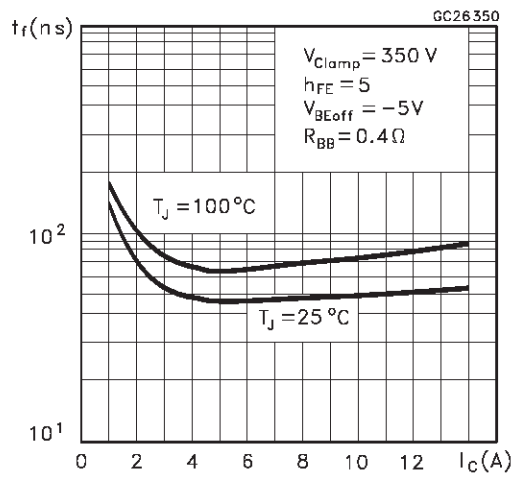
Collector Emitter Saturation Voltage



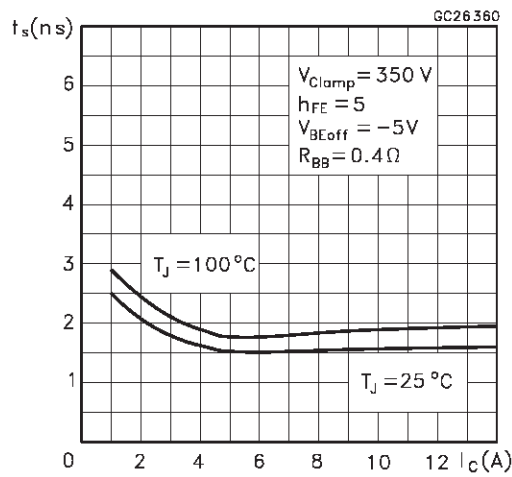
Base Emitter Saturation Voltage



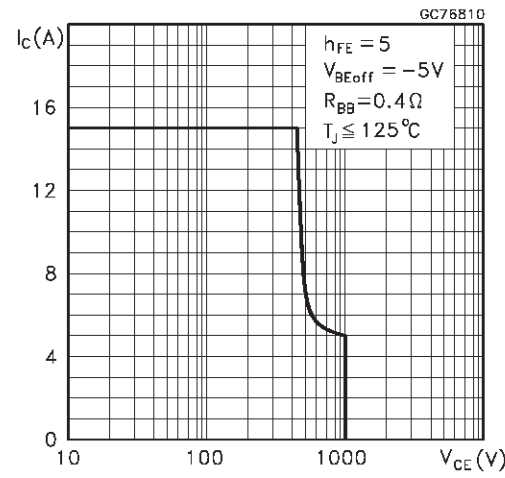
Inductive Fall Time



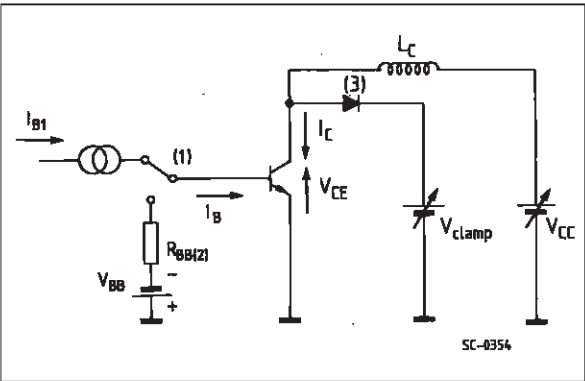
Inductive Storage Time



Reverse Biased SOA



RBSOA and Inductive Load Switching Test Circuits



- (1) Fast electronic switch
- (2) Non-inductive Resistor
- (3) Fast recovery rectifier

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1998 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A